# **Analog Multiplexer/ Demultiplexer**

## **High-Performance Silicon-Gate CMOS**

The MC74LVXT4052 utilizes silicon–gate CMOS technology to achieve fast propagation delays, low ON resistances, and low OFF leakage currents. This analog multiplexer/demultiplexer controls analog voltages that may vary across the complete power supply range (from  $V_{CC}$  to  $V_{EE}$ ).

The LVXT4052 is similar in pinout to the high–speed HC4052A and the metal–gate MC14052B. The Channel–Select inputs determine which one of the Analog Inputs/Outputs is to be connected, by means of an analog switch, to the Common Output/Input. When the Enable pin is HIGH, all analog switches are turned off.

The Channel–Select and Enable inputs are compatible with standard TTL levels.

This device has been designed so the ON resistance ( $R_{ON}$ ) is more linear over input voltage than the  $R_{ON}$  of metal-gate CMOS analog switches and High-Speed CMOS analog switches.

#### **Features**

- Select Pins Compatible with TTL Levels
- Fast Switching and Propagation Speeds
- Low Crosstalk Between Switches
- Analog Power Supply Range  $(V_{CC} V_{EE}) = -3.0 \text{ V}$  to +3.0 V
- Digital (Control) Power Supply Range  $(V_{CC} GND) = 2.5$  to 6.0 V
- Improved Linearity and Lower ON Resistance Than Metal–Gate, HSL, or VHC Counterparts
- Low Noise
- Designed to Operate on a Single Supply with  $V_{EE}$  = GND, or Using Split Supplies up to  $\pm$  3.0 V
- Break-Before-Make Circuitry
- Pb-Free Packages are Available\*

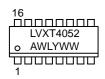


http://onsemi.com

MARKING DIAGRAMS



SOIC-16 D SUFFIX CASE 751B



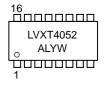


TSSOP-16 DT SUFFIX CASE 948F





SOEIAJ-16 M SUFFIX CASE 966



A = Assembly Location

WL or L = Wafer Lot Y = Year WW or W = Work Week

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

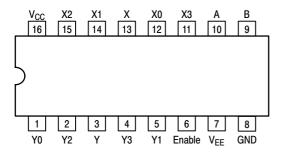
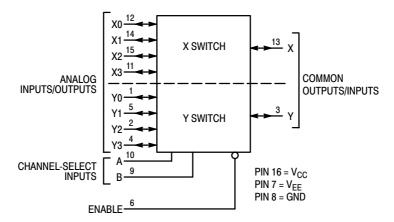


Figure 1. Pin Connection and Marking Diagram (Top View)

#### **FUNCTION TABLE**

Contr	ol Input			
Enable	Se B	lect A	ON Ch	annels
L L L	L H H X	L H L H	Y0 Y1 Y2 Y3	X0 X1 X2 X3

X = Don't Care



NOTE: This device allows independent control of each switch. Channel–Select Input A controls the X–Switch, Input B controls the Y–Switch.

Figure 2. Logic Diagram

Double-Pole, 4-Position Plus Common Off

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74LVXT4052D	SOIC-16	48 Units / Rail
MC74LVXT4052DG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74LVXT4052DR2	SOIC-16	2500 Tape & Reel
MC74LVXT4052DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74LVXT4052DT	TSSOP-16*	96 Units / Rail
MC74LVXT4052DTR2	TSSOP-16*	2500 Tape & Reel
MC74LVXT4052M	SOEIAJ-16	50 Units / Rail
MC74LVXT4052MG	SOEIAJ-16 (Pb-Free)	50 Units / Rail
MC74LVXT4052MEL	SOEIAJ-16	2000 Tape & Reel
MC74LVXT4052MELG	SOEIAJ-16 (Pb-Free)	2000 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>This package is inherently Pb-Free.

#### **MAXIMUM RATINGS**

Symbol		Parameter	Value	Unit
V <sub>EE</sub>	Negative DC Supply Voltage	(Referenced to GND)	-7.0  to  +0.5	V
V <sub>CC</sub>	Positive DC Supply Voltage	(Referenced to GND) (Referenced to $V_{\text{EE}}$ )	- 0.5 to +7.0 - 0.5 to +7.0	V
V <sub>IS</sub>	Analog Input Voltage		$V_{EE} = 0.5 \text{ to } V_{CC} + 0.5$	V
V <sub>IN</sub>	Digital Input Voltage	(Referenced to GND)	-0.5 to 7.0	V
ı	DC Current, Into or Out of Any Pin		±20	mA
T <sub>STG</sub>	Storage Temperature Range		- 65 to +150	°C
TL	Lead Temperature, 1 mm from Case	for 10 Seconds	260	°C
TJ	Junction Temperature under Bias		+ 150	°C
$\theta_{JA}$	Thermal Resistance	SOIC TSSOP	143 164	°C/W
P <sub>D</sub>	Power Dissipation in Still Air,	SOIC TSSOP	500 450	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 30% – 35%	UL 94-V0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	> 2000 > 200 > 1000	V
I <sub>LATCHUP</sub>	Latchup Performance	Above V <sub>CC</sub> and Below GND at 125°C (Note 4)	±300	mA

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- 1. Tested to EIA/JESD22-A114-A.
- 2. Tested to EIA/JESD22-A115-A.
- 3. Tested to JESD22-C101-A.
- 4. Tested to EIA/JESD78.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit	
V <sub>EE</sub>	Negative DC Supply Voltage	(Referenced to GND)	-6.0	GND	V
V <sub>CC</sub>	Positive DC Supply Voltage	(Referenced to GND) (Referenced to V <sub>EE</sub> )	2.5 2.5	6.0 6.0	V
V <sub>IS</sub>	Analog Input Voltage		V <sub>EE</sub>	V <sub>CC</sub>	V
V <sub>IN</sub>	Digital Input Voltage	(Note 5) (Referenced to GND)	0	6.0	V
T <sub>A</sub>	Operating Temperature Range, All Package Types		<del>- 55</del>	125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise/Fall Time (Channel Select or Enable Inputs)	$V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V} $ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	100 20	ns/V

<sup>5.</sup> Unused inputs may not be left open. All inputs must be tied to a high-logic voltage level or a low-logic input voltage level.

## DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

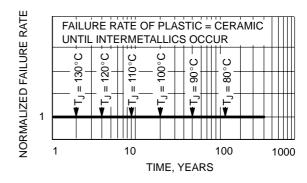


Figure 3. Failure Rate vs. Time Junction Temperature

## DC CHARACTERISTICS - Digital Section (Voltages Referenced to GND)

			V <sub>CC</sub>	Guara			
Symbol	Parameter	Condition	V	−55 to 25°C	≤85°C	≤125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage, Channel-Select or Enable Inputs		3.0 4.5 5.5	2.0 2.0 2.0	2.0 2.0 2.0	2.0 2.0 2.0	V
V <sub>IL</sub>	Maximum Low–Level Input Voltage, Channel–Select or Enable Inputs		3.0 4.5 5.5	0.5 0.8 0.8	0.5 0.8 0.8	0.5 0.8 0.8	V
I <sub>IN</sub>	Maximum Input Leakage Current, Channel–Select or Enable Inputs	V <sub>IN</sub> = 6.0 or GND	0 V to 6.0 V	± 0.1	±1.0	±1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	Channel Select, Enable and $V_{IS} = V_{CC}$ or GND	6.0	4.0	40	80	μΑ

## DC ELECTRICAL CHARACTERISTICS - Analog Section

			V <sub>CC</sub>	V <sub>CC</sub> V <sub>EE</sub> Guaranteed Limit			nit	
Symbol	Parameter	Test Conditions	V	V V	−55 to 25°C	≤ <b>85</b> ° <b>C</b>	≤125°C	Unit
R <sub>ON</sub>	Maximum "ON" Resistance	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{IS} = \frac{1}{2} (V_{CC} - V_{EE})$ $ I_S  = 2.0 \text{ mA (Figure 4)}$	3.0 4.5 3.0	0 0 -3.0	86 37 26	108 46 33	120 55 37	Ω
ΔR <sub>ON</sub>	Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Package	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{IS} = \frac{1}{2} (V_{CC} - V_{EE})$ $ I_S  = 2.0 \text{ mA}$	3.0 4.5 3.0	0 0 -3.0	15 13 10	20 18 15	20 18 15	Ω
I <sub>off</sub>	Maximum Off-Channel Leakage Current, Any One Channel	$V_{in} = V_{IL} \text{ or } V_{IH};$ $V_{IO} = V_{CC} \text{ or GND};$ Switch Off (Figure 3)	5.5 +3.0	0 -3.0	0.1 0.1	0.5 0.5	1.0 1.0	μА
	Maximum Off–Channel Leakage Current, Common Channel	$V_{in} = V_{IL} \text{ or } V_{IH};$ $V_{IO} = V_{CC} \text{ or GND};$ Switch Off (Figure 4)	5.5 +3.0	0 -3.0	0.2 0.2	2.0 2.0	4.0 4.0	
I <sub>on</sub>	Maximum On-Channel Leakage Current, Channel-to-Channel	$V_{in} = V_{IL}$ or $V_{IH}$ ; Switch-to-Switch = $V_{CC}$ or GND; (Figure 5)	5.5 +3.0	0 -3.0	0.2 0.2	2.0 2.0	4.0 4.0	μА

#### **AC CHARACTERISTICS** (Input $t_f = t_f = 3 \text{ ns}$ )

					Guaranteed Limit		nit		
			v <sub>cc</sub>	VEE	-55 to	25°C			
Symbol	Parameter	Test Conditions	٥,	V	Min	Тур*	≤ <b>85</b> ° <b>C</b>	≤125°C	Unit
t <sub>BBM</sub>	Minimum Break-Before-Make	$V_{IN} = V_{IL}$ or $V_{IH}$	3.0	0.0	1.0	6.5	_	-	ns
	Time	$V_{IS} = V_{CC}$	4.5	0.0	1.0	5.0	-	_	
		$R_L$ = 300 Ω, $C_L$ = 35 pF (Figures 12 and 13)	3.0	-3.0	1.0	3.5	-	-	

<sup>\*</sup>Typical Characteristics are at 25°C.

## AC CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 3 \text{ ns}$ )

						Guar	anteed	Limit			
		Vcc	V <sub>EE</sub>	-:	55 to 2	5°C	≤8	5°C	≤12	25°C	
Symbol	Parameter	V	V V	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Channel–Select to Analog Output (Figures 16 and 17)	2.5 3.0 4.5	0 0 0			40 28 23		45 30 25		50 35 30	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Propagation Delay, Enable to Analog Output (Figures 14 and 15)	3.0 2.5 3.0 4.5 3.0	-3.0 0 0 0 -3.0			23 40 28 23 23		25 45 30 25 25		28 50 35 30 28	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Propagation Delay, Enable to Analog Output (Figures 14 and 15)	2.5 3.0 4.5 3.0	0 0 0 -3.0			40 28 23 23		45 30 25 25		50 35 30 28	ns
		•	•	1	ГурісаІ	@ 25°C	, V <sub>CC</sub> =	5.0 V, \	/ <sub>EE</sub> = 0\	/	
$C_{PD}$	Power Dissipation Capacitance (Figure 18) (Note	6)					45				pF
C <sub>IN</sub>	Maximum Input Capacitance, Channel-Select or	Select or Enable Inputs 10			pF						
C <sub>I/O</sub>	Maximum Capacitance (All Switches Off)	Comr	alog I/O non O/I through				10 10 1.0				pF

Feedthrough 1.0

6. Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

#### ADDITIONAL APPLICATION CHARACTERISTICS (GND = 0 V)

			v <sub>cc</sub>	VEE	Тур	
Symbol	Parameter	Condition	٧	V	25°C	Unit
BW	Maximum On–Channel Bandwidth or Minimum Frequency Response	$V_{IS} = \frac{1}{2} (V_{CC} - V_{EE})$ Ref and Test Attn = 10 dB Source Amplitude = 0 dB (Figure 7)	3.0 4.5 6.0 3.0	0.0 0.0 0.0 -3.0	80 80 80 80	MHz
V <sub>ISO</sub>	Off-Channel Feedthrough Isolation	$ f = 1 \text{ MHz; } V_{\text{IS}} = \frac{1}{2} \left( V_{\text{CC}} - V_{\text{EE}} \right) $ Adjust Network Analyzer output to 10 dBm on each output from the power splitter. (Figures 8 and 9)	3.0 4.5 6.0 3.0	0.0 0.0 0.0 -3.0	-70 -70 -70 -70	dB
V <sub>ONL</sub>	Maximum Feedthrough On Loss	V <sub>IS</sub> = ½ (V <sub>CC</sub> – V <sub>EE</sub> ) Adjust Network Analyzer output to 10 dBm on each output from the power splitter. (Figure 11)	3.0 4.5 6.0 3.0	0.0 0.0 0.0 -3.0	-2 -2 -2 -2	dB
Q	Charge Injection	$\begin{array}{c} V_{IN} = V_{CC} \text{ to } V_{EE,}  f_{IS} = 1 \text{ kHz, } t_r = t_f = 3 \text{ ns} \\ R_{IS} = 0  \Omega,  C_L = 1000 \text{ pF, }  Q = C_L * \Delta V_{OUT} \\ \text{(Figure 10)} \end{array}$	5.0 3.0	0.0 -3.0	9.0 12	pC
THD	Total Harmonic Distortion THD + Noise	$\begin{split} f_{IS} &= 1 \text{ MHz, R}_L = 10 \text{ K}\Omega, C_L = 50 \text{ pF,} \\ V_{IS} &= 5.0 \text{ V}_{PP} \text{ sine wave} \\ V_{IS} &= 6.0 \text{ V}_{PP} \text{ sine wave} \\ \text{(Figure 19)} \end{split}$	6.0 3.0	0.0 -3.0	0.10 0.05	%

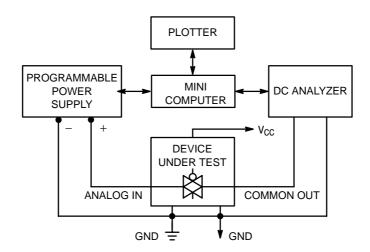
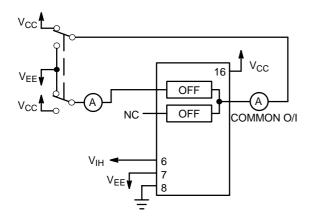


Figure 4. On Resistance, Test Set-Up



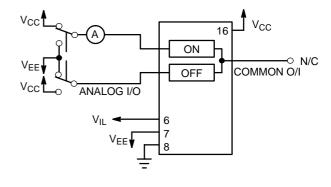


Figure 5. Maximum Off Channel Leakage Current, Any One Channel, Test Set-Up

Figure 6. Maximum On Channel Leakage Current, Channel to Channel, Test Set-Up

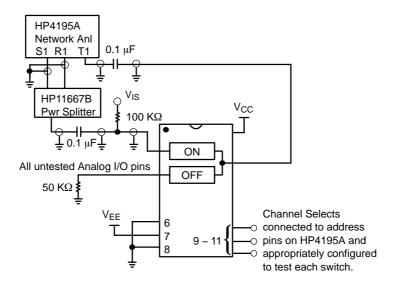


Figure 7. Maximum On Channel Bandwidth, Test Set-Up

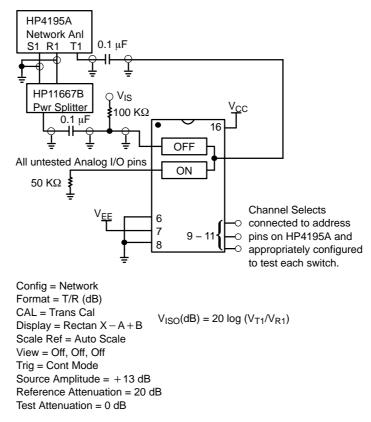


Figure 8. Maximum Off Channel Feedthrough Isolation, Test Set-Up

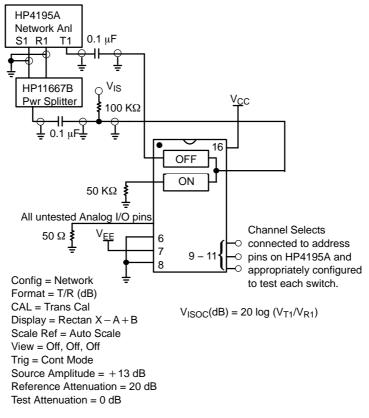
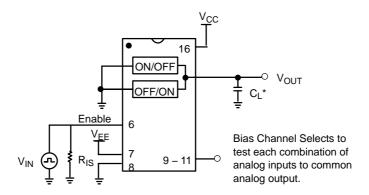


Figure 9. Maximum Common-Channel Feedthrough Isolation, Test Set-Up



\*Includes all probe and jig capacitance.

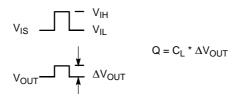


Figure 10. Charge Injection, Test Set-Up

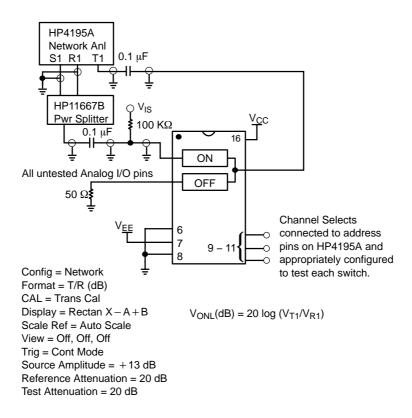


Figure 11. Maximum On Channel Feedthrough On Loss, Test Set-Up

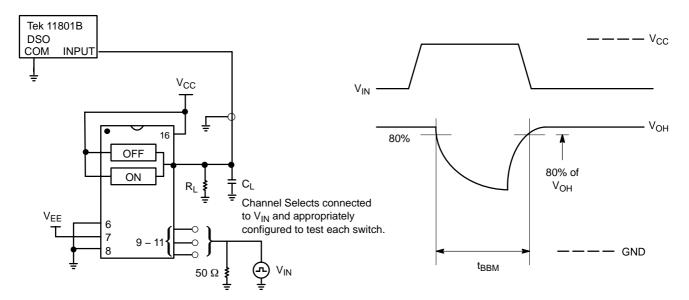


Figure 12. Break-Before-Make, Test Set-Up

Figure 13. Break-Before-Make Time

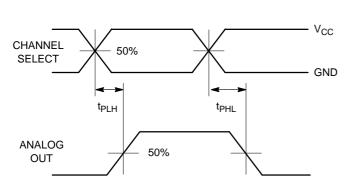
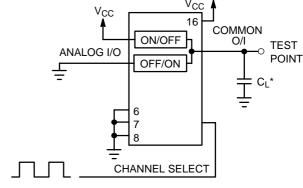


Figure 14. Propagation Delays, Channel Select to Analog Out



\*Includes all probe and jig capacitance.

Figure 15. Propagation Delay, Test Set-Up Channel Select to Analog Out

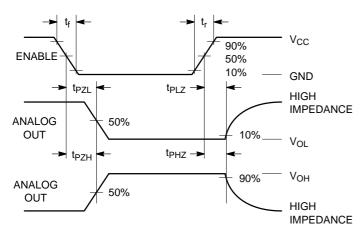


Figure 16. Propagation Delays, Enable to Analog Out

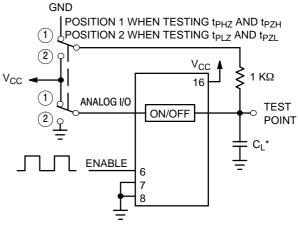


Figure 17. Propagation Delay, Test Set-Up Enable to Analog Out

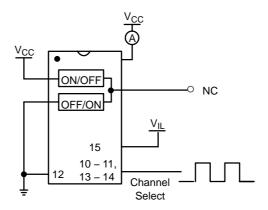


Figure 18. Power Dissipation Capacitance, Test Set-Up

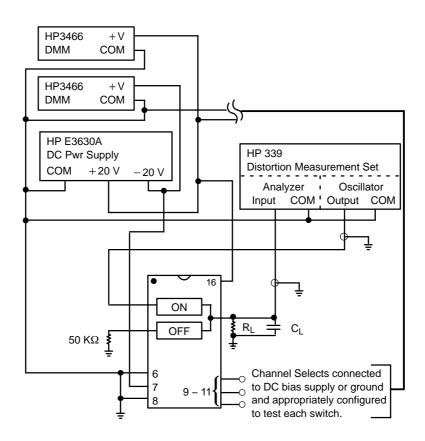


Figure 19. Total Harmonic Distortion, Test Set-Up

#### **APPLICATIONS INFORMATION**

The Channel Select and Enable control pins should be at  $V_{CC}$  or GND logic levels.  $V_{CC}$  being recognized as a logic high and GND being recognized as a logic low. In this example:

$$V_{CC} = +5 \text{ V} = \text{logic high}$$
  
 $GND = 0 \text{ V} = \text{logic low}$ 

The maximum analog voltage swing is determined by the supply voltages  $V_{CC}$  and  $V_{EE}$ . The positive peak analog voltage should not exceed  $V_{CC}$ . Similarly, the negative peak analog voltage should not go below  $V_{EE}$ . In this example, the difference between  $V_{CC}$  and  $V_{EE}$  is five volts. Therefore, using the configuration of Figure 21, a maximum analog signal of five volts peak—to—peak can be controlled. Unused analog inputs/outputs may be left floating (i.e., not connected). However, tying unused analog inputs and

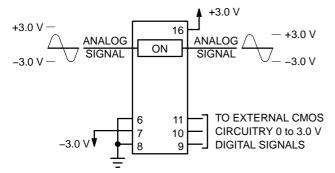


Figure 20. Application Example

outputs to  $V_{CC}$  or GND through a low value resistor helps minimize crosstalk and feedthrough noise that may be picked up by an unused switch.

Although used here, balanced supplies are not a requirement. The only constraints on the power supplies are that:

$$\begin{split} V_{EE} - GND &= 0 \text{ to } -6 \text{ volts} \\ V_{CC} - GND &= 2.5 \text{ to } 6 \text{ volts} \\ V_{CC} - V_{EE} &= 2.5 \text{ to } 6 \text{ volts} \\ \text{and } V_{EE} &\leq GND \end{split}$$

When voltage transients above  $V_{CC}$  and/or below  $V_{EE}$  are anticipated on the analog channels, external Germanium or Schottky diodes  $(D_x)$  are recommended as shown in Figure 22. These diodes should be able to absorb the maximum anticipated current surges during clipping.

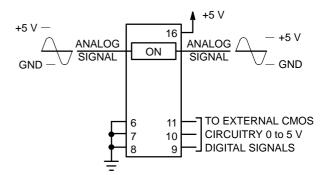


Figure 21. Application Example

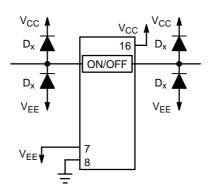


Figure 22. External Germanium or Schottky Clipping Diodes

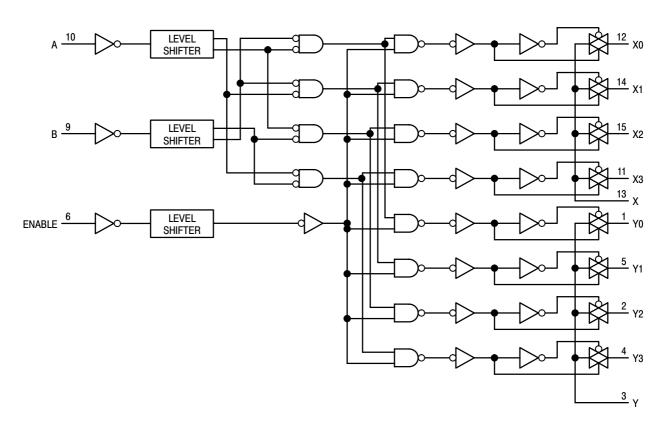
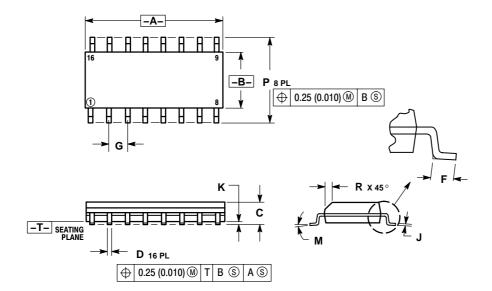


Figure 23. Function Diagram, LVXT4052

#### PACKAGE DIMENSIONS

SOIC-16 **D SUFFIX** CASE 751B-05 **ISSUE J** 



#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

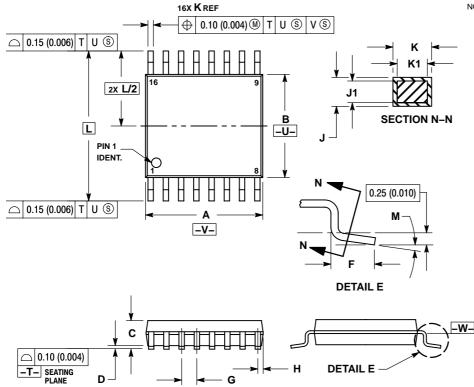
  MAXIMUM MOLD PROTRUSION 0.15 (0.006)

- PEH SIDE.

  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES			
DIM	MIN	MAX	MIN	MAX		
Α	9.80	10.00	0.386	0.393		
В	3.80	4.00	0.150	0.157		
С	1.35	1.75	0.054	0.068		
D	0.35	0.49	0.014	0.019		
F	0.40	1.25	0.016	0.049		
G	1.27	BSC	0.050	BSC		
J	0.19	0.25	0.008	0.009		
K	0.10	0.25	0.004	0.009		
M	0°	7°	0°	7°		
Р	5.80	6.20	0.229	0.244		
R	0.25	0.50	0.010	0.019		

#### TSSOP-16 **DT SUFFIX** CASE 948F-01 **ISSUE A**



- TTES:

  1. DIMENSIONING AND TOLERANCING PER
  ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

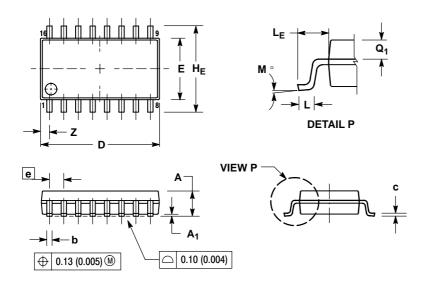
  3. DIMENSION A DOES NOT INCLUDE MOLD
  FLASH. PROTRUSIONS OR GATE BURRS.
  MOLD FLASH OR GATE BURRS SHALL NOT
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.08
- (0.003) TOTAL IN EXCESS OF THE K
  DIMENSION AT MAXIMUM MATERIAL
- DIMENSION AT MAXIMUM MATERIAL
  CONDITION.
  6. TERMINAL NUMBERS ARE SHOWN FOR
  REFERENCE ONLY.
  7. DIMENSION A AND B ARE TO BE
  DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252	BSC
М	0°	8°	0°	8 °

#### SOEIAJ-16 **M SUFFIX** CASE 966-01 **ISSUE O**



#### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE
- PEH SIDE.
  TERMINAL NUMBERS ARE SHOWN FOR
  REFERENCE ONLY.
  THE LEAD WIDTH DIMENSION (b) DOES NOT
  INCLUDE DAMBAR PROTRUSION. ALLOWABLE
  DAMBAR PROTRUSION SHALL BE 0.08 (0.003) DAMBAR PHOTHOSION STALE BE USED (1990)
  TOTAL IN EXCESS OF THE LEAD WIDTH
  DIMENSION AT MAXIMUM MATERIAL CONDITION.
  DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE
  BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 ( 0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Ε	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
$Q_1$	0.70	0.90	0.028	0.035
Z		0.78		0.031

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